**Product data sheet** 

# 1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) plastic package.

## 2. Features and benefits

- Fast switching
- High voltage capability
- · Very low switching and conduction losses

# 3. Applications

- Compact fluorescent lamps (CFL)
- Electronic lighting ballasts
- Inverters
- · Off-line self-oscillating power supplies

# 4. Pinning information

**Table 1. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	В	base		С		
2	С	collector		В		
3	E	emitter		B Than		
			321 TO-92 (SOT54)	sym123		

# 5. Ordering information

**Table 2. Ordering information** 

Type number	Package				
	Name	Description	Version		
PHE13003A	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

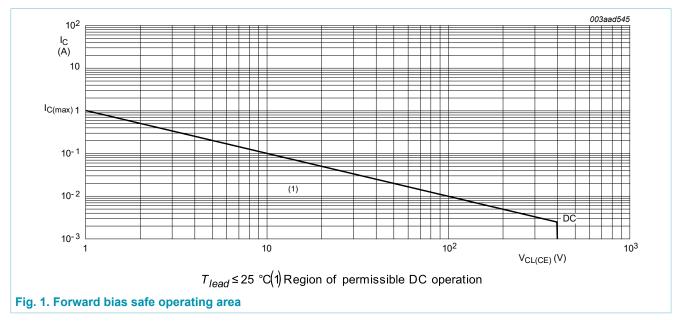
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# 6. Limiting values

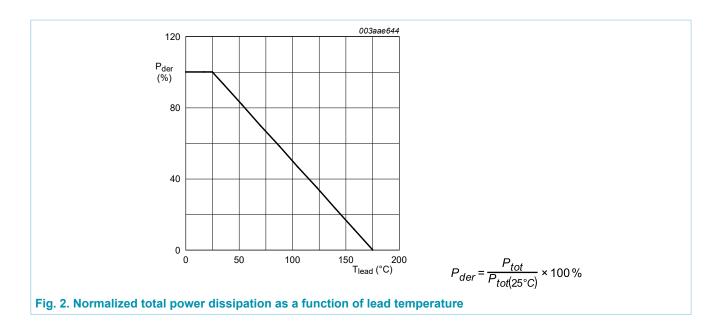
**Table 3. Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	700	V
V <sub>CBO</sub>	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
V <sub>CEO</sub>	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
V <sub>EBO</sub>	emitter-base voltage	I <sub>C</sub> = 0 A; I(Emitter) = 10 mA	-	9	V
I <sub>C</sub>	collector current	DC; Fig. 1	-	1	Α
I <sub>CM</sub>	peak collector current		-	2	Α
I <sub>B</sub>	base current	DC	-	0.5	Α
I <sub>BM</sub>	peak base current		-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 2</u>	-	2.1	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C



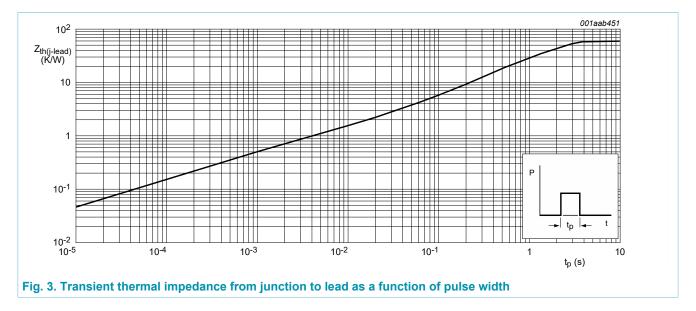
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## 7. Thermal characteristics

**Table 4. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	<u>Fig. 3</u>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



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## 8. Characteristics

## **Table 5. Characteristics**

Symbol	Parameter	Conditions	M	in Typ	Max	Unit
Static chara	acteristics					
I <sub>CES</sub>	collector-emitter cut-off current (base shorted)	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 125 \text{ °C}$	-	-	5	mA
I <sub>EBO</sub>	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	1	mA
$V_{CEOsus}$	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25 \text{ °C}; \underline{Fig. 4}; \underline{Fig. 5}$	40	00 -	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 0.25 A; $I_B$ = 50 mA; $T_{lead}$ = 25 °C; Fig. 6	-	0.2	0.5	V
		$I_C$ = 0.5 A; $I_B$ = 125 mA; $T_{lead}$ = 25 °C; Fig. 6	-	0.3	1	V
		$I_C$ = 0.75 A; $I_B$ = 250 mA; $T_{lead}$ = 25 °C; Fig. 6	-	0.4	1.5	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 0.25 \text{ A}$ ; $I_B = 50 \text{ mA}$ ; $T_{lead} = 25 ^{\circ}\text{C}$ ; Fig. 7	-	-	1	V
		$I_C$ = 0.5 A; $I_B$ = 125 mA; $T_{lead}$ = 25 °C; Fig. 7	-	-	1.2	V
h <sub>FE</sub>	DC current gain	$I_C$ = 0.5 mA; $V_{CE}$ = 2 V; $T_{lead}$ = 25 °C; Fig. 8; Fig. 9	12	2 -	-	
		$I_C = 0.4 \text{ A}; V_{CE} = 5 \text{ V}; T_{lead} = 25 ^{\circ}\text{C};$ Fig. 8; Fig. 9	10	) -	30	
		I <sub>C</sub> = 0.8 A; V <sub>CE</sub> = 5 V; T <sub>lead</sub> = 25 °C; <u>Fig. 8</u> ; <u>Fig. 9</u>	5	7.5	20	
Dynamic ch	aracteristics					
t <sub>f</sub>	fall time	$I_C$ = 1 A; $I_{Bon}$ = 200 mA; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{lead}$ = 25 °C; inductive load; Fig. 10; Fig. 11	-	80	-	ns

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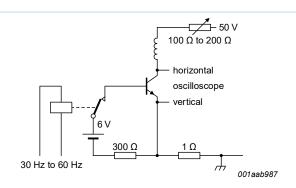


Fig. 4. Test circuit for collector-emitter sustaining voltage

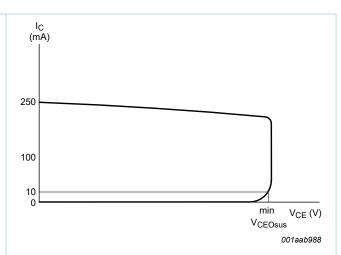


Fig. 5. Oscilloscope display for collector-emitter sustaining voltage test waveform

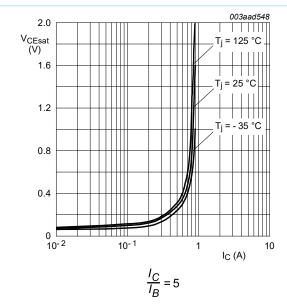


Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

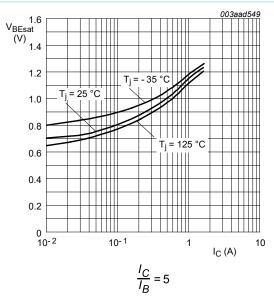


Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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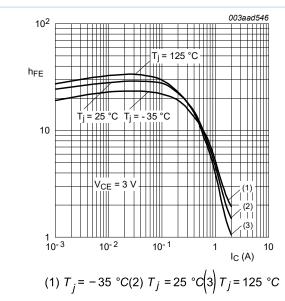


Fig. 8. DC current gain as a function of collector current; typical values

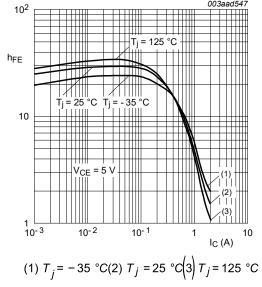
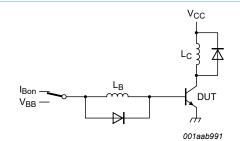


Fig. 9. DC current gain as a function of collector current; typical values



 $V_{CC} = 300 \ V; V_{BB} = -5 \ V; L_C = 200 \ \mu H; L_B = 1 \ \mu H$ 

Fig. 10. Test circuit for inductive load switching

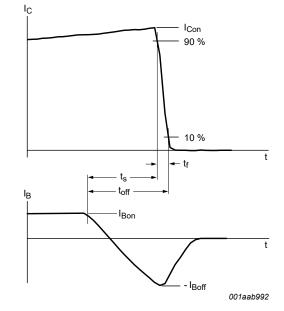


Fig. 11. Switching times waveforms for inductive load

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# 9. Package outline

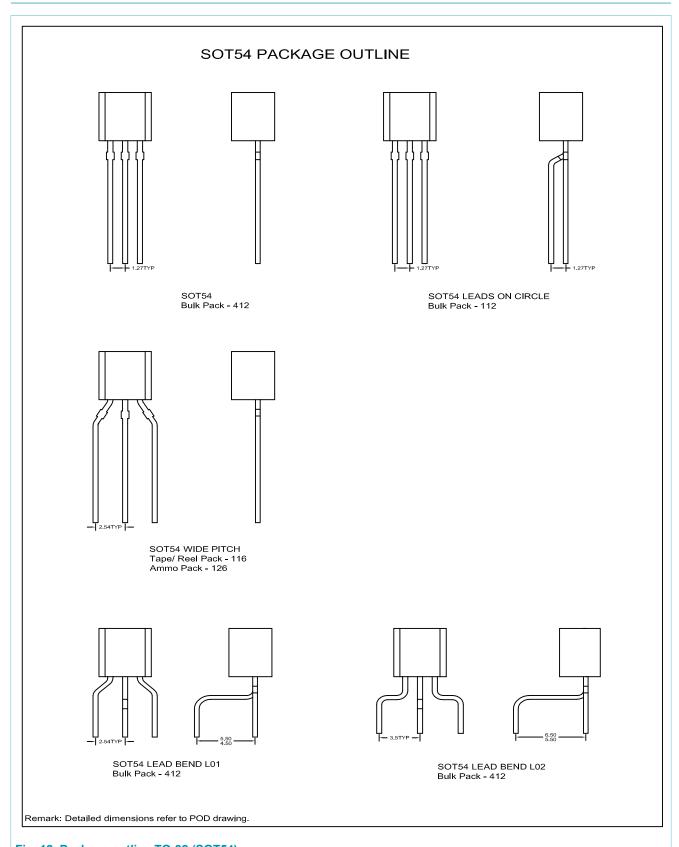


Fig. 12. Package outline TO-92 (SOT54)

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# 10. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet		This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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